

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

- 1 21. (withdrawn): A method of fabricating a gap insulation layer upon a substrate layer in a
2 read head, including the steps of:
 - 3 a. depositing a thin film of metal on a substrate layer;
 - 4 b. oxidizing said thin film of metal to form a first metal oxide lamination;
 - 5 c. depositing a second sheet of metal on top of the first lamination;
 - 6 d. oxidizing the second sheet of metal to form a second lamination; and
 - 7 e. repeating steps c and d to fabricate a multilayer laminated structure of a desired
8 thickness.

- 1 22. (withdrawn): The method as recited in claim 21, wherein each lamination is formed of an
2 oxide of a metal selected from the group consisting of aluminum, silicon, chromium, and
3 tantalum.

- 1 23. (withdrawn): The method as recited in claim 21, wherein each lamination in the
2 multilayer structure is formed of a nitride of a metal selected from the group consisting of
3 aluminum, silicon, chromium and tantalum.

- 1 24. (withdrawn): The method as recited in claim 21, wherein the multilayer laminated
2 structure is composed of approximately 5-10 laminations.

- 1 25. (withdrawn): The method as recited in claim 24, wherein the preferred thickness of each
2 lamination is approximately 10A to 50 A.

1 26. (withdrawn): The method as recited in claim 25, wherein the thickness of each
2 lamination is approximately 10 Å to 20 Å.

1 37. (currently amended): A method for fabricating a magnetic head, said method
2 comprising:

3 depositing a first magnetic shield layer upon a wafer substrate;
4 depositing a first gap insulation layer upon a said first magnetic shield layer;
5 fabricating a sensor upon said first gap insulation layer;
6 fabricating the electrical leads proximate to said sensor, said leads providing electrical
7 current to said sensor;

8 fabricating a second gap insulation layer upon said electrical leads and said sensor, said
9 second gap insulation ~~layer~~ layer including a first gap insulation layer portion that is fabricated
10 upon said electrical leads, and a second gap insulation layer portion that is fabricated upon both
11 said sensor and said first gap insulation layer portion, and wherein said first and second gap
12 insulation layer portions are made up of a plurality of multilayered laminations; and

13 fabricating a second magnetic shield upon said second gap insulation layer.

1 38. (currently amended): A method according to claim 37, [[']] wherein the step of
2 fabricating said second gap insulation layer includes the substeps of fabricating said first gap
3 insulation layer portion by:

4 a. depositing a thin film of metal on ~~a substrate layer~~ said electrical leads;
5 b. oxidizing said thin film of metal to form a first metal oxide lamination;
6 c. depositing a second sheet of metal on top of the first lamination;
7 d. oxidizing the second sheet of metal to form a second lamination; and
8 e. repeating steps c and d to achieve a multilayer laminated structure of a desired
9 thickness; and

10 fabricating said second gap insulation layer portion by:

11 f. depositing a thin film of metal on said sensor and said first gap insulation layer
12 portion;

13 g. oxidizing said thin film of metal to form a first metal oxide lamination;

- 14 h. depositing a second sheet of metal on top of the first lamination;
15 i. oxidizing the second sheet of metal to form a second lamination; and
16 j. repeating steps c and d to achieve a multilayer laminated structure of a desired
17 thickness.

1 39. (original): The method as recited in claim 38, wherein each lamination in the multilayer
2 structure is formed of an oxide of a metal selected from the group consisting of aluminum,
3 silicon, chromium, and tantalum.

1 40. (original): The method as recited in claim 38, wherein each lamination in the multilayer
2 structure is formed of a nitride of a metal selected from the group consisting of aluminum,
3 silicon, chromium and tantalum.

1 41. (currently amended): The method as recited in claim 38, wherein the multilayer structure
2 of each of said first gap insulation layer portion and said second gap insulation layer portion is
3 composed of approximately 5-10 laminations.

1 42. (original): The method as recited in claim 38, wherein the thickness of each lamination is
2 approximately 10Å to 50 Å.

1 43. (original): The method as recited in claim 38, wherein the preferred thickness of each
2 lamination is approximately 10 Å to 20 Å.